



# SPN1423

## N-Channel Enhancement Mode MOSFET

### DESCRIPTION

The SPN1423 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching , and low in-line power loss are needed in a very small outline surface mount package.

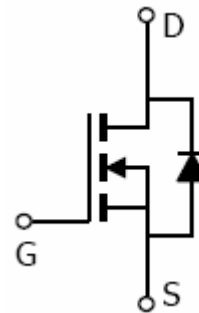
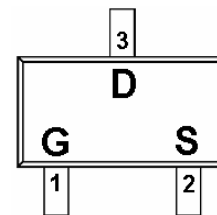
### FEATURES

- ◆ 20V/2.8A,  $R_{DS(ON)} = 90m\Omega @ V_{GS} = 4.5V$
- ◆ 20V/2.2A,  $R_{DS(ON)} = 100m\Omega @ V_{GS} = 2.5V$
- ◆ Super high density cell design for extremely low  $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-323 ( SC-70 ) package design

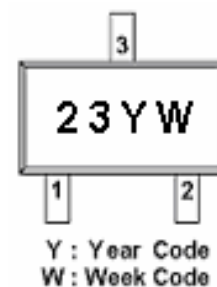
### APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

### PIN CONFIGURATION ( SOT-323 ; SC-70 )



### PART MARKING





# SPN1423

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### PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPN1423S32RG	SOT-323	23YW

Week Code : A ~ Z( 1 ~ 26 ) ; a ~ z( 27 ~ 52 )

SPN1423S32RG : Tape Reel ; Pb – Free

### ABSOLUTE MAXIMUM RATINGS

(TA=25 Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V <sub>DSS</sub>	20	V
Gate –Source Voltage	V <sub>GSS</sub>	±12	V
Continuous Drain Current(T <sub>J</sub> =150 )	I <sub>D</sub>	2.8	A
		2.2	
Pulsed Drain Current	I <sub>DM</sub>	10	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	1.6	A
Power Dissipation	P <sub>D</sub>	0.33	W
		0.21	
Operating Junction Temperature	T <sub>J</sub>	150	
Storage Temperature Range	T <sub>STG</sub>	-55/150	
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	100	/W

**SPN1423****N-Channel Enhancement Mode MOSFET****ELECTRICAL CHARACTERISTICS**(T<sub>A</sub>=25 Unless otherwise noted)

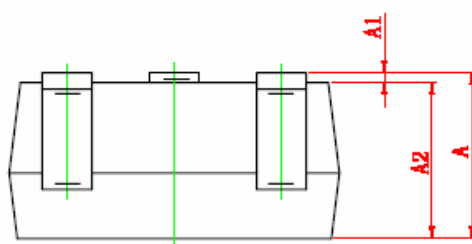
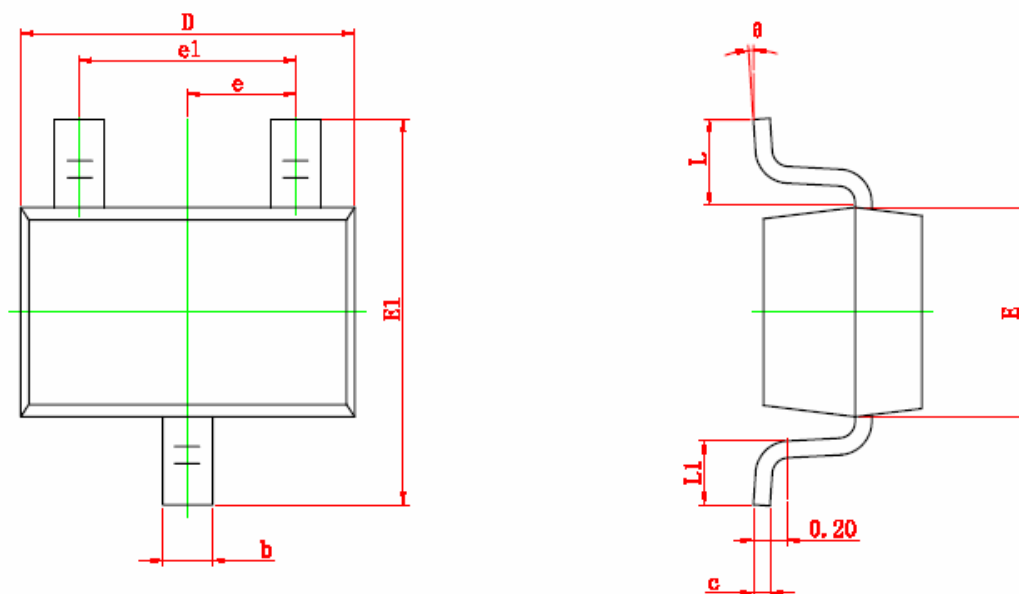
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.45		1.2	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA
		V <sub>DS</sub> =20V, V <sub>GS</sub> =0V T <sub>J</sub> =55			10	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> =4.5V	5			A
		V <sub>DS</sub> = 5V, V <sub>GS</sub> =2.5V	4			
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.8A		0.055	0.090	Ω
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.2A		0.075	0.100	
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =2.8A		10		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.6A, V <sub>GS</sub> =0V		0.85	1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V I <sub>D</sub> =2.8A		5.4	10	nC
Gate-Source Charge	Q <sub>gs</sub>			0.65		
Gate-Drain Charge	Q <sub>gd</sub>			1.4		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V f=1MHz		340		pF
Output Capacitance	C <sub>oss</sub>			115		
Reverse Transfer Capacitance	C <sub>rss</sub>			33		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, R <sub>L</sub> =5.5Ω I <sub>D</sub> =2.8A, V <sub>GEN</sub> =4.5V R <sub>G</sub> =6Ω		12	25	ns
	t <sub>r</sub>			36	60	
Turn-Off Time	t <sub>d(off)</sub>			34	60	
	t <sub>f</sub>			10	25	



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### SOT-323 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°



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